



Future Normal in Semiconductor

2025년 2월 13일(목), 15:50-17:20

Room J(스페이스 II+III), 6층

J. Nano-Science & Technology 분과

O36_[TJ3-J] 2D Devices & Materials

좌장: 권지민 교수(UNIST), 조경준 교수(한국과학기술원)

<p>초청 TJ3-J-1 15:50-16:20</p>	<p>Process Emulation and Device Simulation of Gate-All-Around MoS₂ Nanosheet NMOSFET Sung-Min Hong and In Ki Kim School of Electrical Engineering and Computer Science, GIST</p>
<p>TJ3-J-2 16:20-16:35</p>	<p>Investigation of Optimal Architecture with MoS₂ Channel Gate-All-Around FETs Based on 0.7nm Process Node Junyeol Lee and Jongwook Jeon Department of Electrical and Computer Engineering, Sungkyunkwan University</p>
<p>TJ3-J-3 16:35-16:50</p>	<p>Large-Area Implementation of Double-Gate Vertical Sidewall MoS₂ Field-Effect Transistors for Area-Efficient Integrated Circuit Jiwon Ma¹ and Jiwon Chang^{1, 2} ¹Department of Materials Science and Engineering, Yonsei University, ²Department of System Semiconductor Engineering, Yonsei University</p>
<p>TJ3-J-4 16:50-17:05</p>	<p>Manipulating Thermal Conductivity of Monolayer MoS₂ by All-Scale Hierarchical Phonon Scattering through Multi-Scale Defects Mingyu Jang¹, Jeongin Yeo², Seonguk Yang², Sungkyu Kim³, Lina Yang⁴, and Joonki Suh^{1,2} ¹Graduate School of Semiconductor Materials and Devices Engineering, UNIST, ²Department of Materials Science and Engineering, UNIST, ³Department of Nanotechnology and Advanced Materials Engineering, Sejong University, ⁴ School of Aerospace Engineering, Beijing Institute of Technology</p>
<p>TJ3-J-5 17:05-17:20</p>	<p>Explainable AI-Driven Insights into the Correlation of Raman Spectroscopy and Reduction Degree in Graphene Oxide Jaekak Yoo¹, Youngwoo Cho², Dong Hyeon Kim¹, Seung Mi Lee³, Jaegul Choo², and Mun Seok Jeong¹ ¹Hanyang University, ²KAIST, ³KRISS,</p>